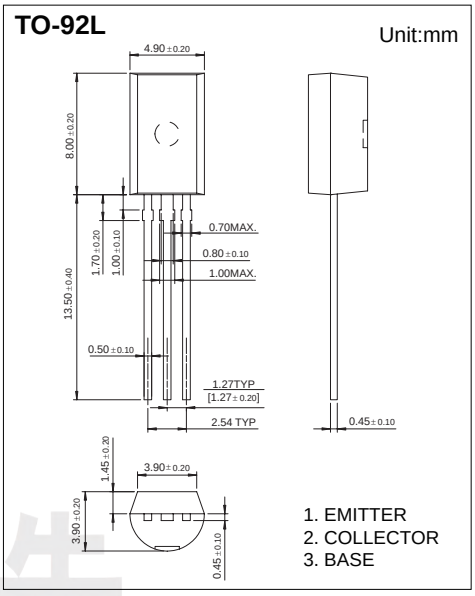
PNP Transistors

D5610



■ Features

- ● Excellent Linearity of Current Gain
- ● Low saturation voltage
- ● Complementary to D5609

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-25	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-1	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CBO}	I_C= -10 μA， I_E=0	-25			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B=0	-20			
Emitter - base breakdown voltage	V_{EBO}	I_E= -10 μA， I_C=0	-5			
Collector cut-off current	I_{CBO}	V_{CB}= -20 V , I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800 mA, I_B= -80 mA			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-800 mA, I_B= -80 mA			-1.2	
Base-emitter voltage	V_{BE}	V_{CE} =-2V, I_C =-500mA			-1	
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -500mA	60		240	
Output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		38		pF
Transition frequency	f_T	V_{CE}= -2V, I_C= -500mA		350		MHz

■ Classification of hFE

Rank	A	B	C
Range	60-120	85-170	120-240